

Form PTO-1449  
(Rev. 8-83)U.S. Department of Commerce  
Patent and Trademark Office

Atty D cket 0756-2345

Serial No. N/A

## INFORMATION DISCLOSURE STATEMENT

Applicants: Shunpei YAMAZAKI et al.

Filing Date: July 31, 2001

Group Art Unit

JUL 31 2001 U.S. PTO



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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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Examiner *Thien Kane* Date Considered 02-20-04

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Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Atty Docket 0756-2345		Serial No. N/A	
<b>INFORMATION DISCLOSURE STATEMENT</b>				Applicants: Shunpei YAMAZAKI et al.			
				Filing Date: July 31, 2001		Group Art Unit: 2811	
<b>FOREIGN PATENT DOCUMENTS</b>							
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes      No	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	09/917,633
				Filing Date	July 31, 2001
				First Named Inventor	Shunpei YAMAZAKI et al.
				Group Art Unit	2811
				Examiner Name	
Sign _____ of _____ _____				Attorney Docket Number	740756-2345

## U.S. PATENT DOCUMENTS

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## FOREIGN PATENT DOCUMENTS

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## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.

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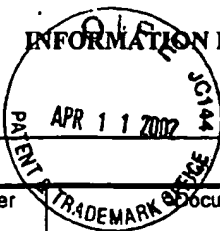
Serial No. 09/917,633

## INFORMATION DISCLOSURE STATEMENT

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						Yes	No
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				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	740756-2345

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